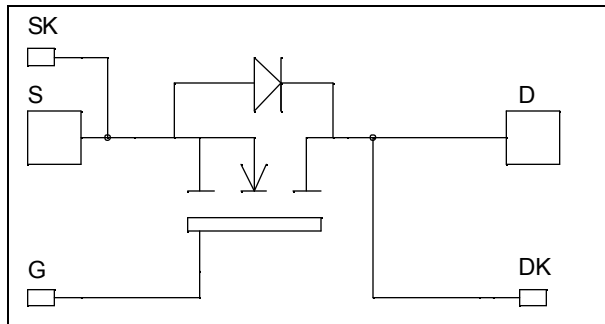


Single Switch MOSFET Power Module

$$V_{DSS} = 1000V$$

$$R_{DSon} = 45m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 215A \text{ @ } T_c = 25^\circ C$$

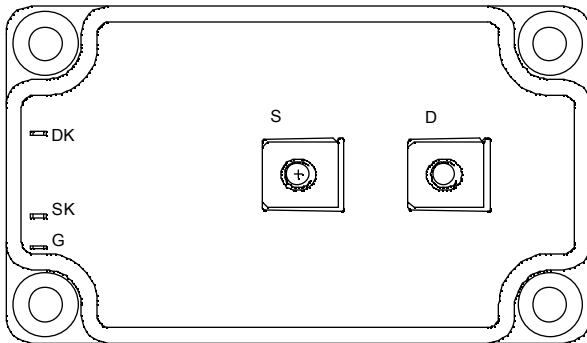


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance



Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{DM}	Pulsed Drain current	860	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	52	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	5000
I_{AR}	Avalanche current (repetitive and non repetitive)	30	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3200	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1000V$ $T_j = 25^\circ\text{C}$			600	μA
		$V_{GS} = 0V, V_{DS} = 800V$ $T_j = 125^\circ\text{C}$			3	mA
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 107.5A$		45	52	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 30\text{mA}$	3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 600	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		42.7		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		7.6		
C_{rss}	Reverse Transfer Capacitance	$f = 1\text{MHz}$		1.3		
Q_g	Total gate Charge	$V_{GS} = 10V$		1602		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 500V$		204		
Q_{gd}	Gate – Drain Charge	$I_D = 215A$		1038		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 670V$ $I_D = 215A$ $R_G = 0.5\Omega$		18		ns
T_r	Rise Time			14		
$T_{d(off)}$	Turn-off Delay Time			140		
T_f	Fall Time			55		
E_{on}	Turn-on Switching Energy	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 215A, R_G = 0.5\Omega$		7.2		mJ
E_{off}	Turn-off Switching Energy			4.3		
E_{on}	Turn-on Switching Energy	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 670V$ $I_D = 215A, R_G = 0.5\Omega$		12		mJ
E_{off}	Turn-off Switching Energy			5.8		

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I _S	Continuous Source current (Body diode)		T _C = 25°C			215	A
			T _C = 80°C			160	
V _{SD}	Diode Forward Voltage	V _{GS} = 0V, I _S = - 215A				1.3	V
dv/dt	Peak Diode Recovery ❶					18	V/ns
t _{rr}	Reverse Recovery Time	I _S = - 215A V _R = 670V di _S /dt = 600A/μs	T _j = 25°C			310	ns
			T _j = 125°C			625	
Q _{rr}	Reverse Recovery Charge		T _j = 25°C		12		μC
			T _j = 125°C		36		

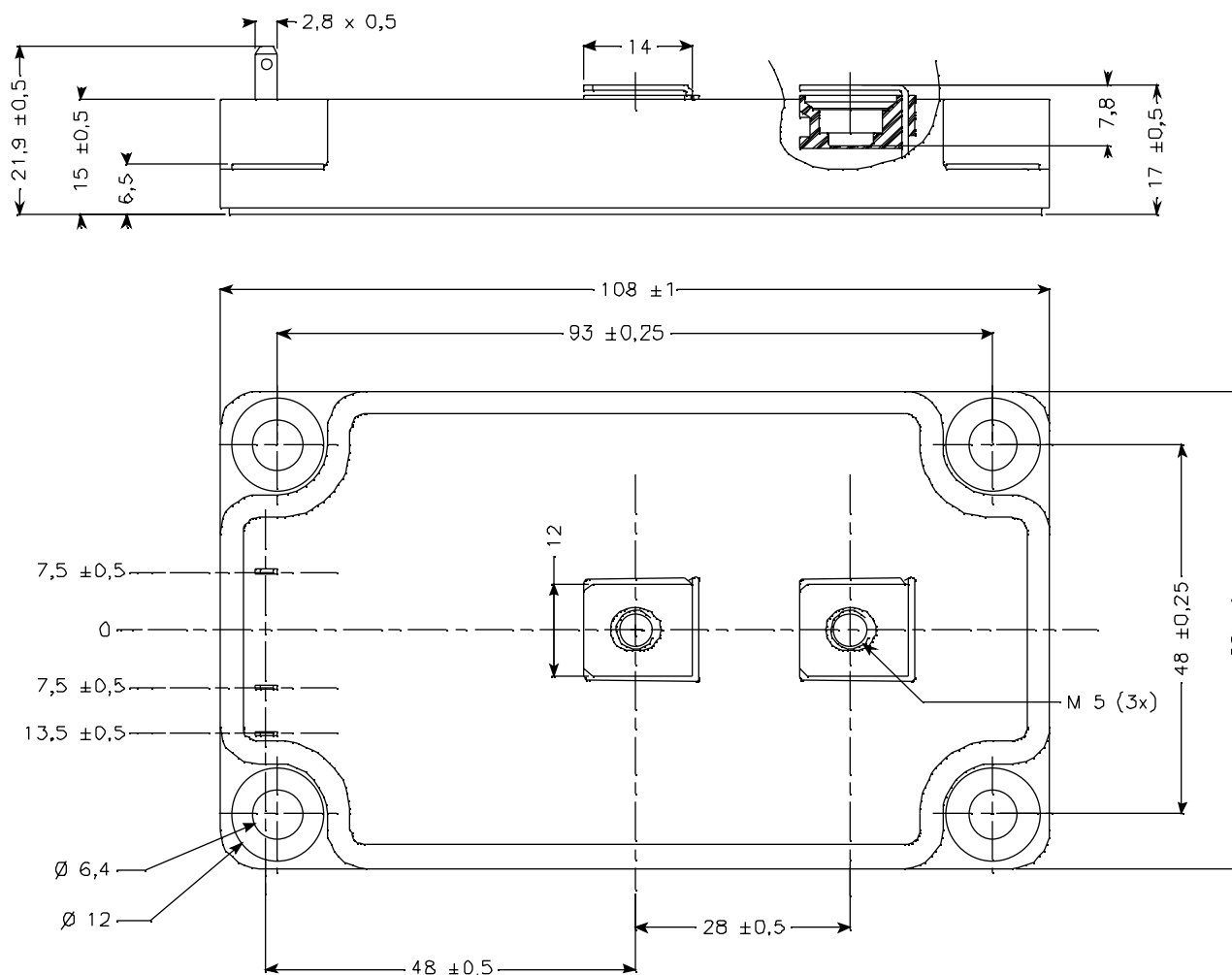
❶ dv/dt numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -215A \quad di/dt \leq 700A/\mu\text{s} \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ\text{C}$$

Thermal and package characteristics

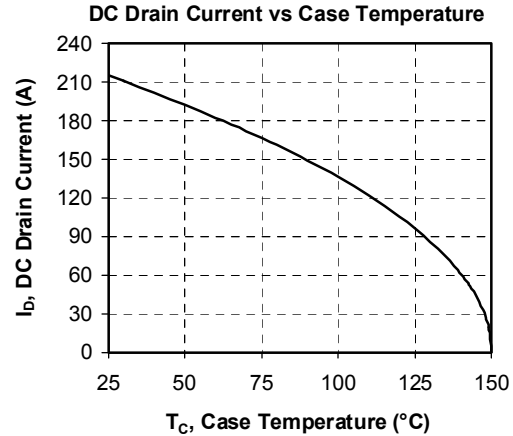
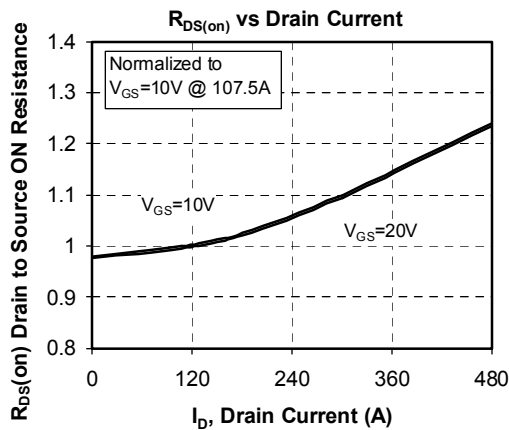
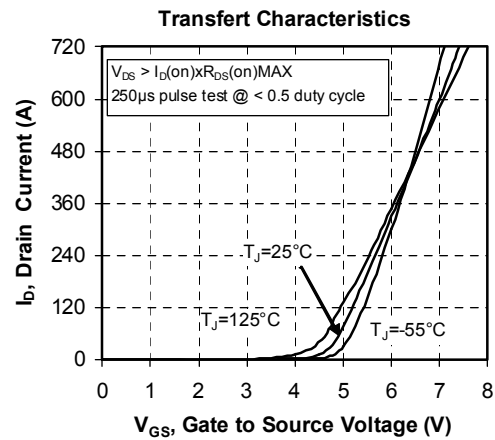
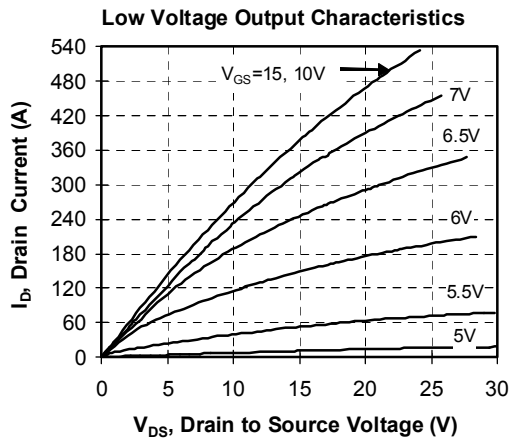
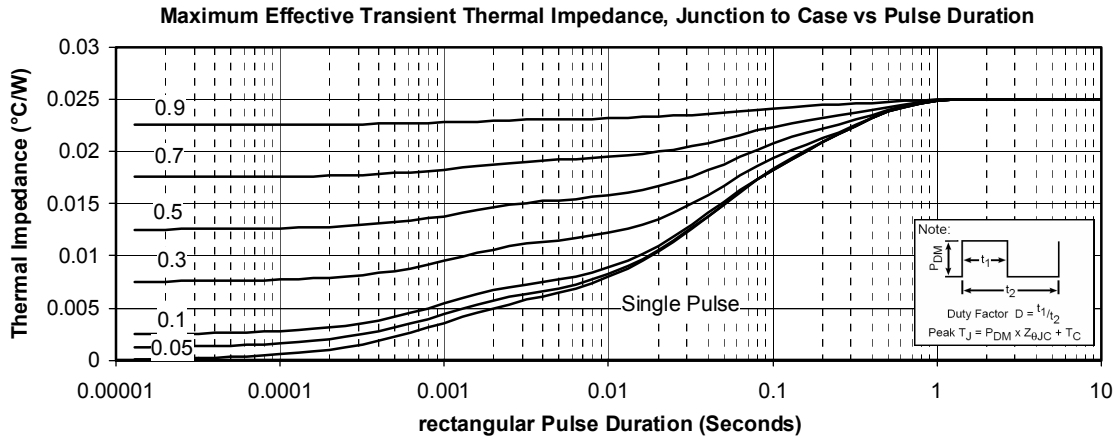
Symbol	Characteristic	Min	Typ	Max	Unit
R _{thJC}	Junction to Case Thermal Resistance			0.025	°C/W
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz	2500			V
T _J	Operating junction temperature range	-40		150	°C
T _{STG}	Storage Temperature Range	-40		125	
T _C	Operating Case Temperature	-40		100	
Torque	Mounting torque	To Heatsink	M6	3	N.m
		For teminals	M5	2	
Wt	Package Weight			280	g

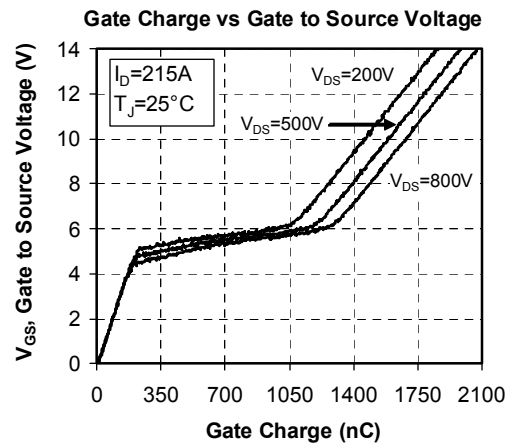
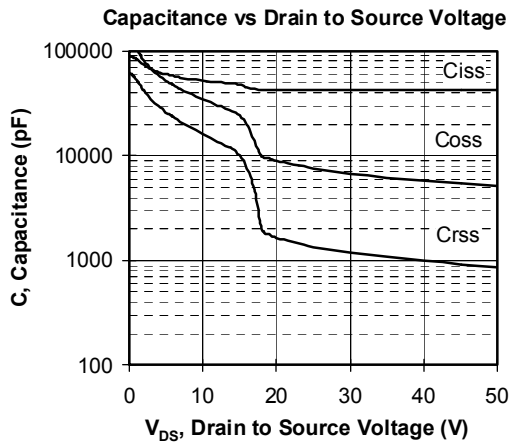
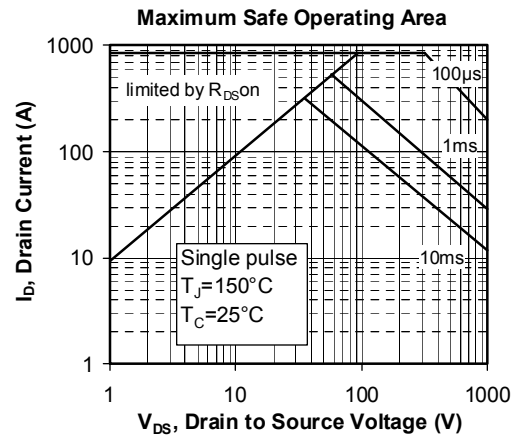
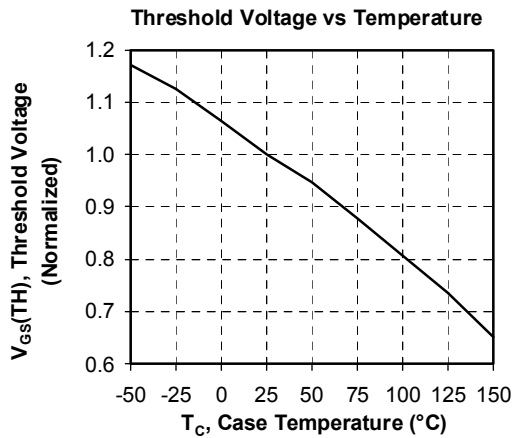
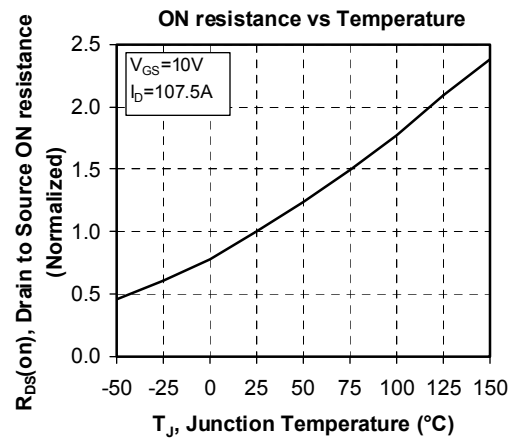
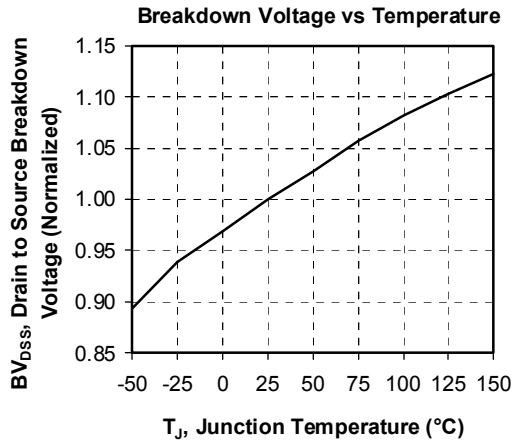
SP6 Package outline (dimensions in mm)

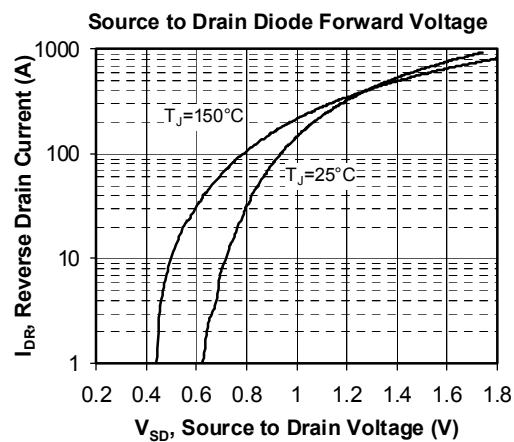
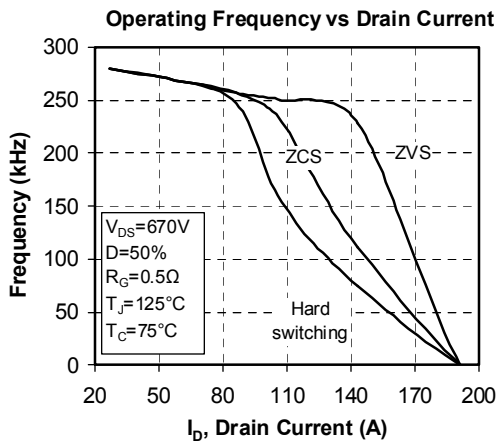
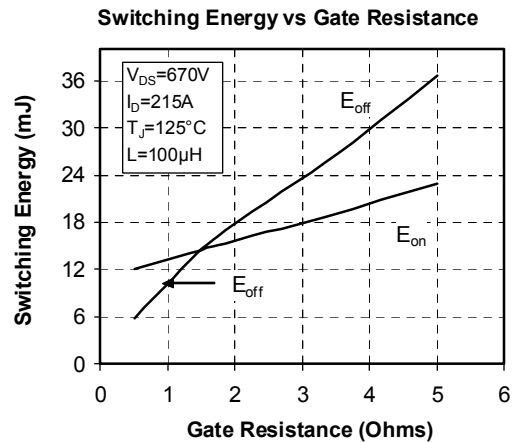
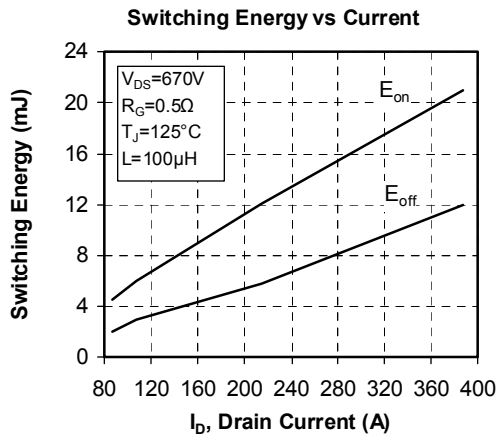
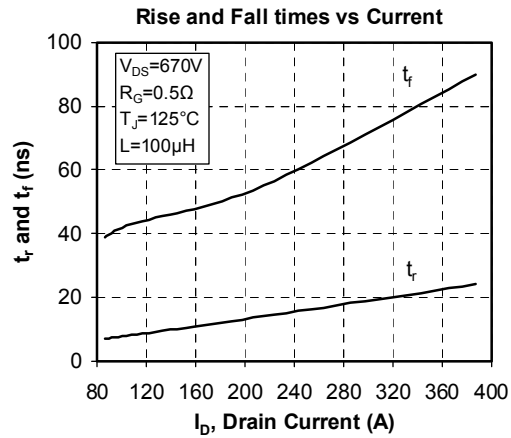
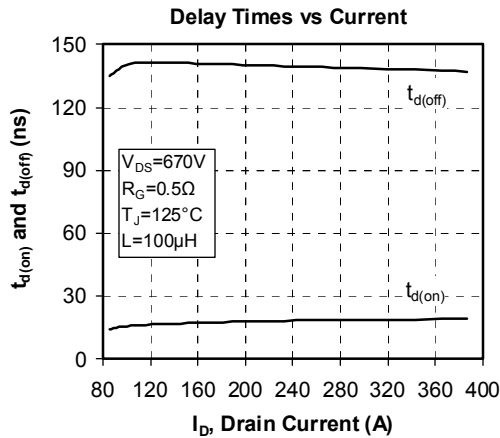


See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

Typical Performance Curve







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